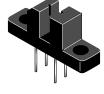


- 1. Dimensions for all drawings are in inches (mm).
- 2. Tolerance of ± .010 (.25) on all non-nominal dimensions unless otherwise specified.

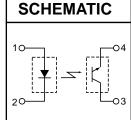
DESCRIPTION

The H21A1, H21A2 and H21A3 consist of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.



FEATURES

- Opaque housing
- · Low cost
- .035" apertures
- High I_{C(ON)}



- 1. Derate power dissipation linearly 1.33 mW/°C above 25°C.
- 2. RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron tip 1/16" (1.6mm) minimum from housing.

| Parameter | Symbol | Rating | Unit | |
|--|--------------------|----------------|---------------------------------------|--|
| Operating Temperature | T _{OPR} | -55 to +100 | °C | |
| Storage Temperature | T _{STG} | -55 to +100 | °C | |
| Soldering Temperature (Iron)(2,3 and 4) | T _{SOL-I} | 240 for 5 sec | °C | |
| Soldering Temperature (Flow)(2 and 3) | T _{SOL-F} | 260 for 10 sec | °C | |
| INPUT (EMITTER) | | 50 | A | |
| Continuous Forward Current | lF | 50 | mA | |
| Reverse Voltage | V _R | 6 | V | |
| Power Dissipation (1) | P _D | 100 | mW | |
| OUTPUT (SENSOR) | | 20 | \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | |
| Collector to Emitter Voltage | V _{CEO} | 30 | V | |
| Emitter to Collector Voltage | V _{ECO} | 4.5 | V | |
| Collector Current | I _C | 20 | mA | |
| Power Dissipation (T _C = 25°C) ⁽¹⁾ | P _D | 150 | mW | |



| ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C)(All measurements made under pulse condition) | | | | | | | | | | |
|--|---|--------------------|---------|------|-----|------|-------|--|--|--|
| PARAMETER | TEST CONDITIONS | SYMBOL | DEVICES | MIN | TYP | MAX | UNITS | | | |
| INPUT (EMITTER) Forward Voltage | I _F = 60 mA | VF | All | _ | _ | 1.7 | V | | | |
| Reverse Breakdown Voltage | I _R = 10 μA | V_R | All | 6.0 | _ | _ | V | | | |
| Reverse Leakage Current | V _R = 3 V | I _R | All | _ | _ | 1.0 | μA | | | |
| OUTPUT (SENSOR) Emitter to Collector Breakdown | $I_F = 100 \mu A, Ee = 0$ | BV _{ECO} | All | 6.0 | | _ | V | | | |
| Collector to Emitter Breakdown | $I_{\rm C} = 1 \text{ mA, Ee} = 0$ | BV _{CEO} | All | 30 | _ | _ | V | | | |
| Collector to Emitter Leakage | V _{CE} = 25 V, Ee = 0 | I _{CEO} | All | _ | _ | 100 | nA | | | |
| COUPLED | I _F = 5 mA, V _{CE} = 5 V | I _{C(ON)} | H21A1 | 0.15 | _ | _ | mA | | | |
| On-State Collector Current | | | H21A2 | 0.30 | _ | _ | | | | |
| | | | H21A3 | 0.60 | _ | _ | | | | |
| | $I_F = 20 \text{ mA}, V_{CE} = 5 \text{ V}$ | | H21A1 | 1.0 | _ | _ | | | | |
| | | | H21A2 | 2.0 | _ | _ | | | | |
| | | | H21A3 | 4.0 | | | | | | |
| | | | H21A1 | 1.9 | _ | _ | | | | |
| | $I_F = 30 \text{ mA}, V_{CE} = 5 \text{ V}$ | | H21A2 | 3.0 | _ | _ | | | | |
| | | | H21A3 | 5.5 | _ | _ | | | | |
| Saturation Voltage | $I_F = 20 \text{ mA}, I_C = 1.8 \text{ mA}$ | VCE(SAT) | H21A2/3 | _ | _ | 0.40 | V | | | |
| | $I_F = 30 \text{ mA}, I_C = 1.8 \text{ mA}$ | | H21A1 | | _ | 0.40 | V | | | |
| Turn-On Time | $I_F = 30$ mA, $V_{CC} = 5$ V, $R_L = 2.5$ K Ω | t _{on} | All | | 8 | | μs | | | |
| Turn-Off Time | $I_F = 30$ mA, $V_{CC} = 5$ V, $R_L = 2.5$ K Ω | t _{off} | All | | 50 | _ | μs | | | |



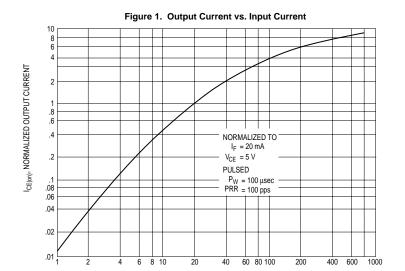
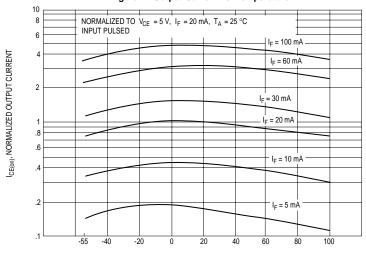


Figure 2. Output Current vs. Temperature

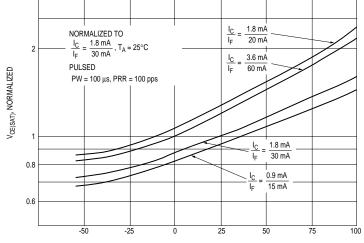
IF, INPUT CURRENT (mA)



T_A, AMBIENT TEMPERATURE (°C)

Figure 3. V_{CE(SAT)} vs. Temperature

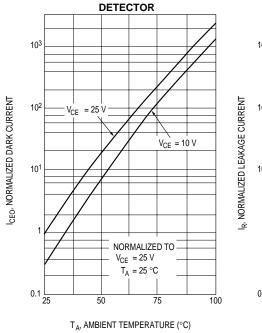


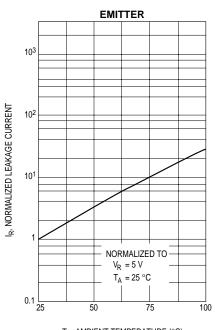


TA, AMBIENT TEMPERATURE (°C)



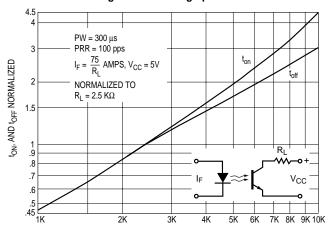
Figure 4. Leakage Current vs. Temperature



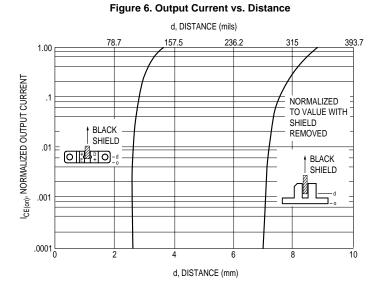


T_A, AMBIENT TEMPERATURE (°C)

Figure 5. Switching Speed vs. RL



 R_L , LOAD RESISTANCE (Ω)



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